Triacs BT137 series

GENERAL DESCRIPTION

Passivated triacs in a plastic envelope, intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

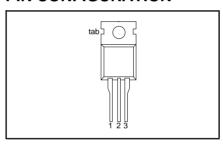
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
	BT137- BT137- BT137-	500 500F 500G	600 600F 600G	800 800F 800G	
V_{DRM}	Repetitive peak off-state	500	600	800	V
I _{T(RMS)} I _{TSM}	voltages RMS on-state current Non-repetitive peak on-state current	8 65	8 65	8 65	A A

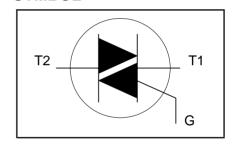
PINNING - TO220AB

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
tab	main terminal 2

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
V_{DRM}	Repetitive peak off-state voltages		-	-500 500 ¹	-600 600 ¹	-800 800	V
$I_{T(RMS)}\\I_{TSM}$	RMS on-state current Non-repetitive peak on-state current	full sine wave; $T_{mb} \le 102 ^{\circ}\text{C}$ full sine wave; $T_{j} = 25 ^{\circ}\text{C}$ prior to surge	-		8		A
		t = 20 ms t = 16.7 ms	-		65 71		A
l²t dl _⊤ /dt	I ² t for fusing Repetitive rate of rise of on-state current after	t = 10.7 ms t = 10 ms $I_{TM} = 12 \text{ A}; I_G = 0.2 \text{ A};$ $dI_{G}/dt = 0.2 \text{ A}/\mu\text{s}$	-		21		A A²s
	triggering	T2+ G+ T2+ G- T2- G-	- - -		50 50 50		A/μs A/μs A/μs
I _{GM} V _{GM} P _{GM}	Peak gate current Peak gate voltage Peak gate power	T2- G+	- - -		10 2 5 5		A/μs A V W
P _{G(AV)} T _{stg} T _j	Average gate power Storage temperature Operating junction temperature	over any 20 ms period	- -40 -		0.5 150 125		O°,

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6 $A/\mu s$.

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Thermal resistance junction to mounting base Thermal resistance junction to ambient	full cycle half cycle in free air		- - 60	2.0 2.4 -	K/W K/W K/W

STATIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.		MAX.		UNIT
		BT137-				F	G	
I_{GT}	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$						
		T2+ G+	-	5	35	25	50	mA
		T2+ G-	-	8	35	25	50	mA
		T2- G-	-	11	35	25	50	mA
		T2- G+	-	30	70	70	100	mA
IL	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$						
_		T2+ G+	-	7	30	30	45	mA
		T2+ G-	-	16	45	45	60	mA
		T2- G-	-	5	30	30	45	mA
		T2- G+	-	7	45	45	60	mA
I_{H}	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	5	20	20	40	mA
V_T	On-state voltage	I _τ = 10 A	_	1.3		1.65		V
V_{GT}	Gate trigger voltage	$\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$	-	0.7		1.5		V
0.		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A};$	0.25	0.4		-		V
		T _i = 125 °C						
I_D	Off-state leakage current	$V_D = V_{DRM(max)};$ $T_i = 125 °C$	-	0.1		0.5		mA

DYNAMIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.		TYP.	MAX.	UNIT
dV _D /dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)};$ $T_i = 125 °C;$ exponential	 100	F 50	G 200	250	-	V/μs
dV _{com} /dt	Critical rate of change of commutating voltage	waveform; gate open circuit $V_{DM} = 400 \text{ V}; T_j = 95 ^{\circ}\text{C};$ $I_{T(RMS)} = 8 \text{ A};$ $dI_{com}/dt = 3.6 \text{ A/ms}; gate$	-	-	10	20	-	V/μs
t_{gt}	Gate controlled turn-on time	open circuit $I_{TM} = 12 \text{ A}; V_D = V_{DRM(max)}; I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A}/\mu s$	-	-	-	2	-	μs

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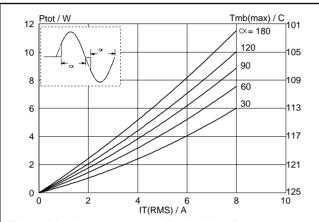


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where α = conduction angle.

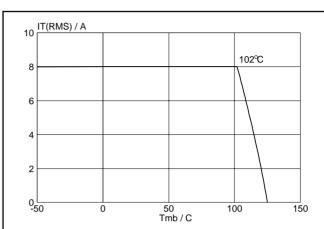


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb} .

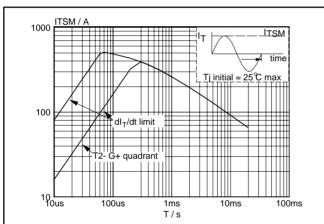


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 20$ ms.

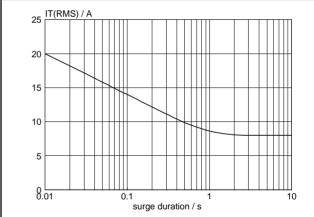


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{mb} \le 102$ °C.

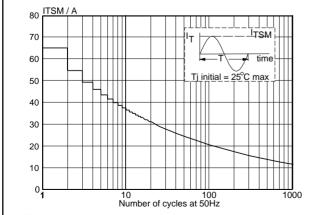


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

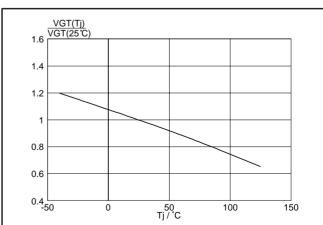
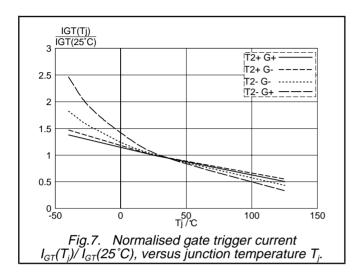


Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/V_{GT}(25^{\circ}C)$, versus junction temperature T_j .

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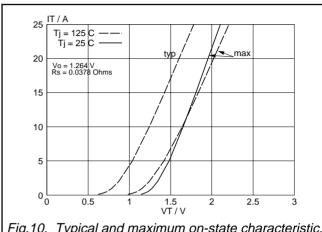
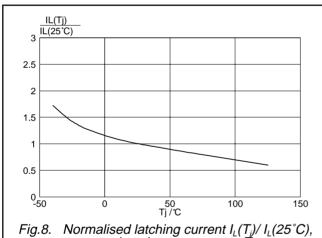


Fig. 10. Typical and maximum on-state characteristic.



versus junction temperature T

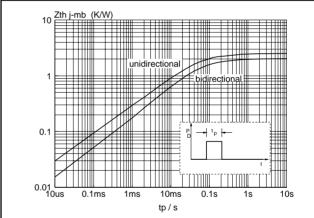


Fig.11. Transient thermal impedance $Z_{th i-mb}$, versus pulse width t_n.

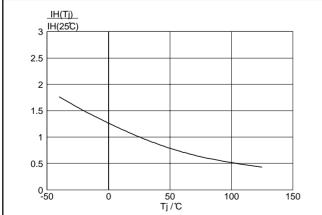


Fig.9. Normalised holding current $I_H(T_i)/I_H(25^{\circ}C)$, versus junction temperature T_i .

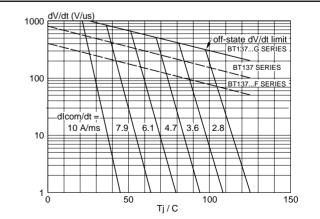
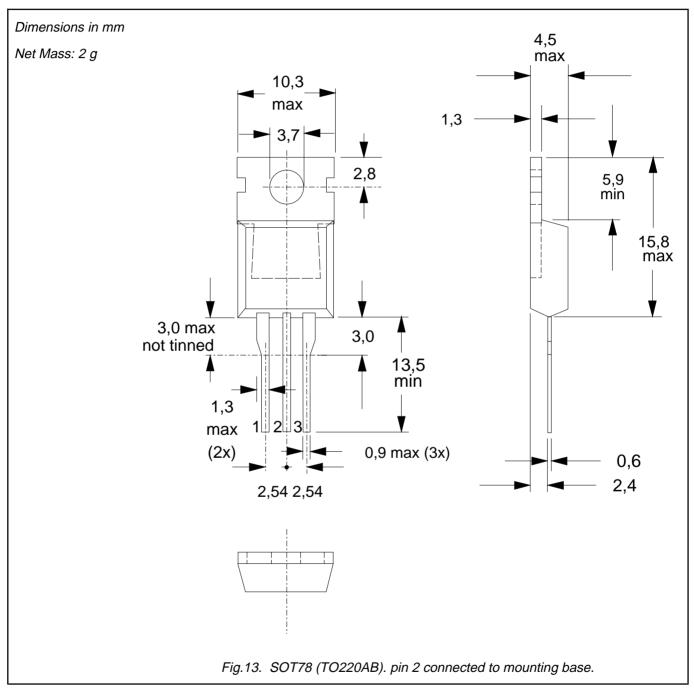


Fig.12. Typical commutation dV/dt versus junction temperature, parameter commutation dl₁/dt. The triac should commutate when the dV/dt is below the value on the appropriate curve for pre-commutation dI_{τ}/dt .

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MECHANICAL DATA



- Notes
 1. Refer to mounting instructions for SOT78 (TO220) envelopes.
 2. Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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